



# **Digital transistors**

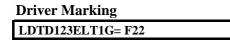
#### Features

 Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
The bias resistors consist of thinfilm resistors with complete isolation to allow negative biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.

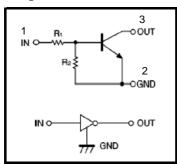
**3)Only the on/off conditions need to be set for operation, making device design easy.** 

**%**Vdeclare that the material of product compliance with **BS**Irequirements.

•Structure NPN digital transistor (Built-in resistor type)

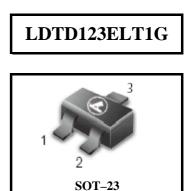


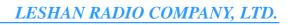
#### •Equivalent circuit



#### **Ordering Information**

Device	Marking	Shipping
LDTD123ELT1G	F22	3000/Tape&Reel
LDTD123ELT3G	F22	10000/Tape&Reel







#### LDTD123ELT1G

Deremeter	Symbol	Limits(D	1 In it	
Parameter		к	S	Unit
Supply voltage	Vcc	50		v
Input voltage	VIN	-10~+12		V
Output current	lc	500		mA
Power dissipation	Pd	200	300	mW
Junction temperature	Tj	150		ĉ
Storage temperature	Tstg	-55~+150		°C

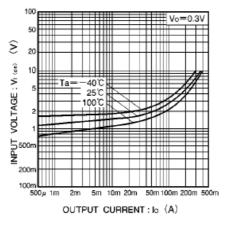
### •Absolute maximum ratings (Ta = $25^{\circ}$ C)

#### •Electrical characteristics (Ta = $25^{\circ}$ C)

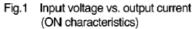
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Input voltage	VI(off)	—	—	0.5	v	Vcc=5V, Io=100 µ A	
	VI(on)	3	-	-	Ý	Vo=0.3V, Io=20mA	
Output voltage	VO(on)	—	0.1	0.3	V	lo/li=50mA/2.5mA	
Input current	h	—	—	3.8	mA	Vi=5V	
Output current	O(off)	—	-	0.5	μA	Vcc=50V, Vi=0V	
DC current gain	Gi	39	—	_	_	Vo=5V, Io=50mA	
Input resistance	R1	1.54	2.2	2.86	kΩ	—	
Resistance ratio	R2/R1	0.8	1	1.2	_	_	
Transition frequency	fт	_	200	_	MHz	Vce=10V, Ie=-5mA, f=100MHz	*



#### LDTD123ELT1G



•Electrical characteristic curves



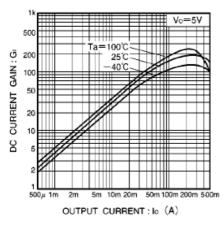


Fig.3 DC current gain vs. output current

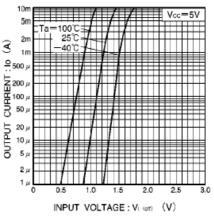


Fig.2 Output current vs. input voltage (OFF characteristics)

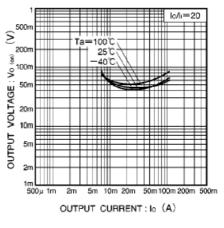


Fig.4 Output voltage vs. output current

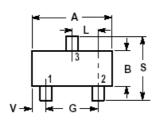


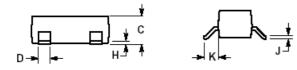
#### LDTD123ELT1G

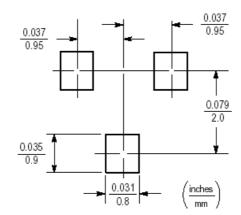
#### SOT-23

NOTES: 1.DIMENSIONING AND TOLERANCING PER ANSI Y14.5M,1982 2.CONTROLLING DIMENSION:INCH

DIM	IN	ICHES	MILLIMETERS		
2	MIN	MAX	MIN	MAX	
Α	0.1102	0.1197	2.80	3.04	
В	0.0472	0.0551	1.20	1.40	
С	0.0350	0.0440	0.89	1.11	
D	0.0150	0.0200	0.37	0.50	
G	0.0701	0.0807	1.78	2.04	
н	0.0005	0.0040	0.013	0.100	
J	0.0034	0.0070	0.085	0.177	
к	0.0140	0.0285	0.35	0.69	
L	0.0350	0.0401	0.89	1.02	
S	0.0830	0.1039	2.10	2.64	
v	0.0177	0.0236	0.45	0.60	

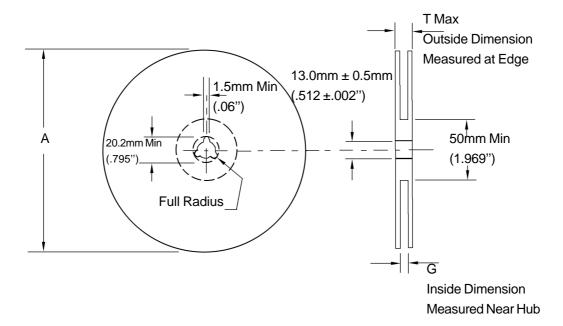








# EMBOSSED TAPE AND REEL DATA FOR DISCRETES



Size	A Max	G	T Max
8 mm	330mm	8.4mm+1.5mm, -0.0	14.4mm
	(12.992")	(.33"+.059", -0.00)	(.56")

#### **Reel Dimensions**

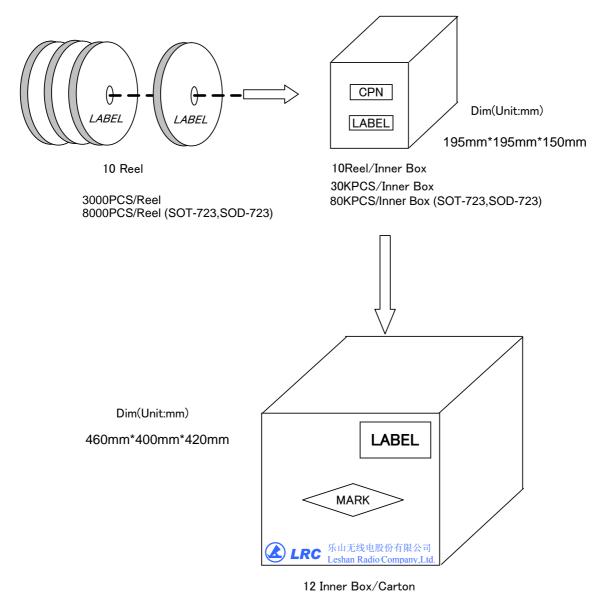
Metric Dimensions Govern — English are in parentheses for reference only

Storage Conditions

Temperature: 5 to 40 Deg.C (20 to 30 Deg. C is preferred) Humidity: 30 to 80 RH (40 to 60 is preferred) Recommended Period: One year after manufacturing (This recommended period is for the soldering condition only. The characteristics and reliabilities of the products are not restricted to this limitation)



# **Shipment Specification**



360KPCS/Carton 960KPCS/Carton (SOT-723,SOD-723)